

# DESIGN AND CRYOGENIC CHARACTERIZATION OF INTEGRATED CIRCUITS FOR QUANTUM COMPUTING

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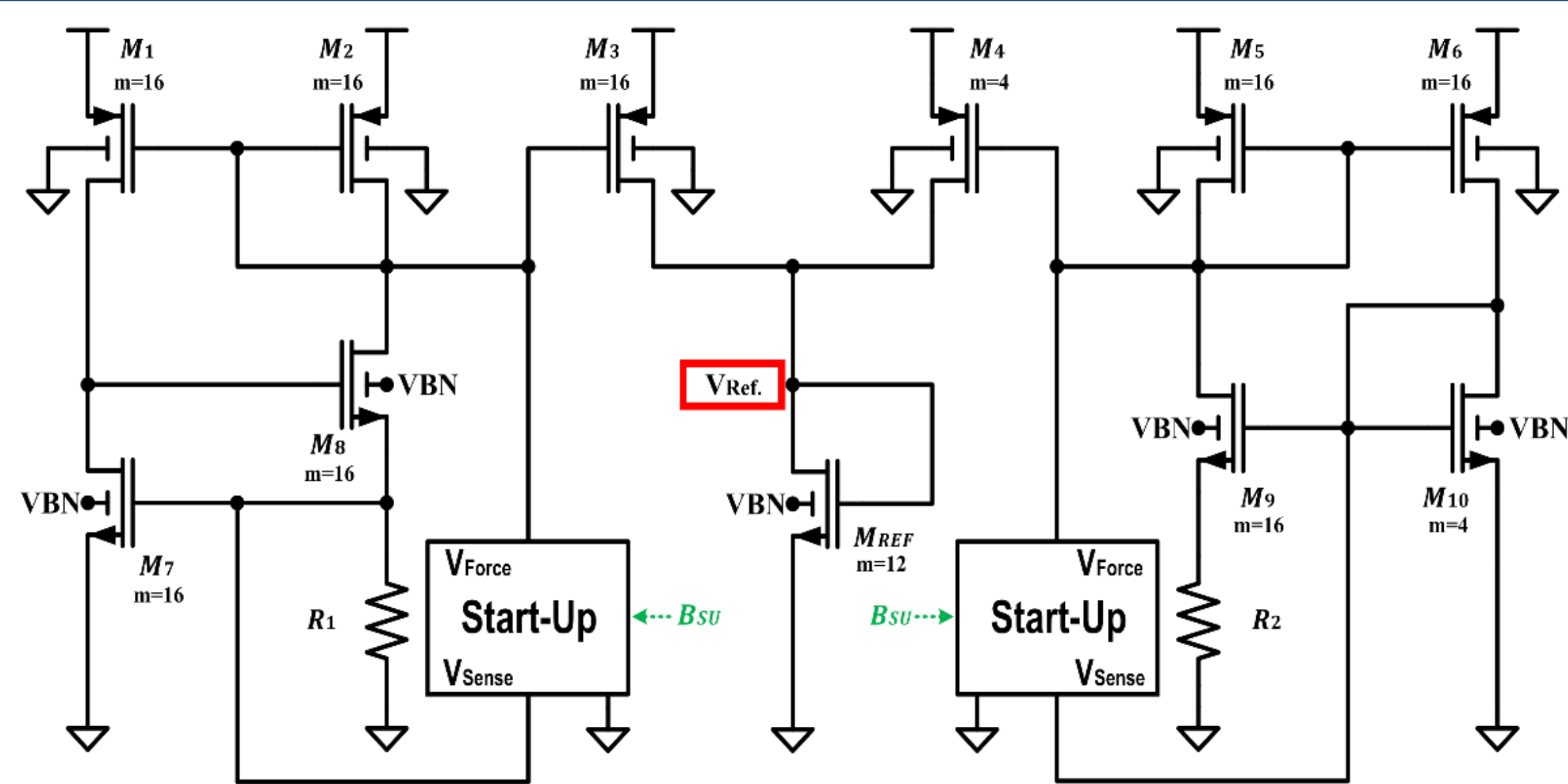


Fig. 1: Cryogenic voltage reference based on cryogenic  $V_{th}$  saturation phenomenon.

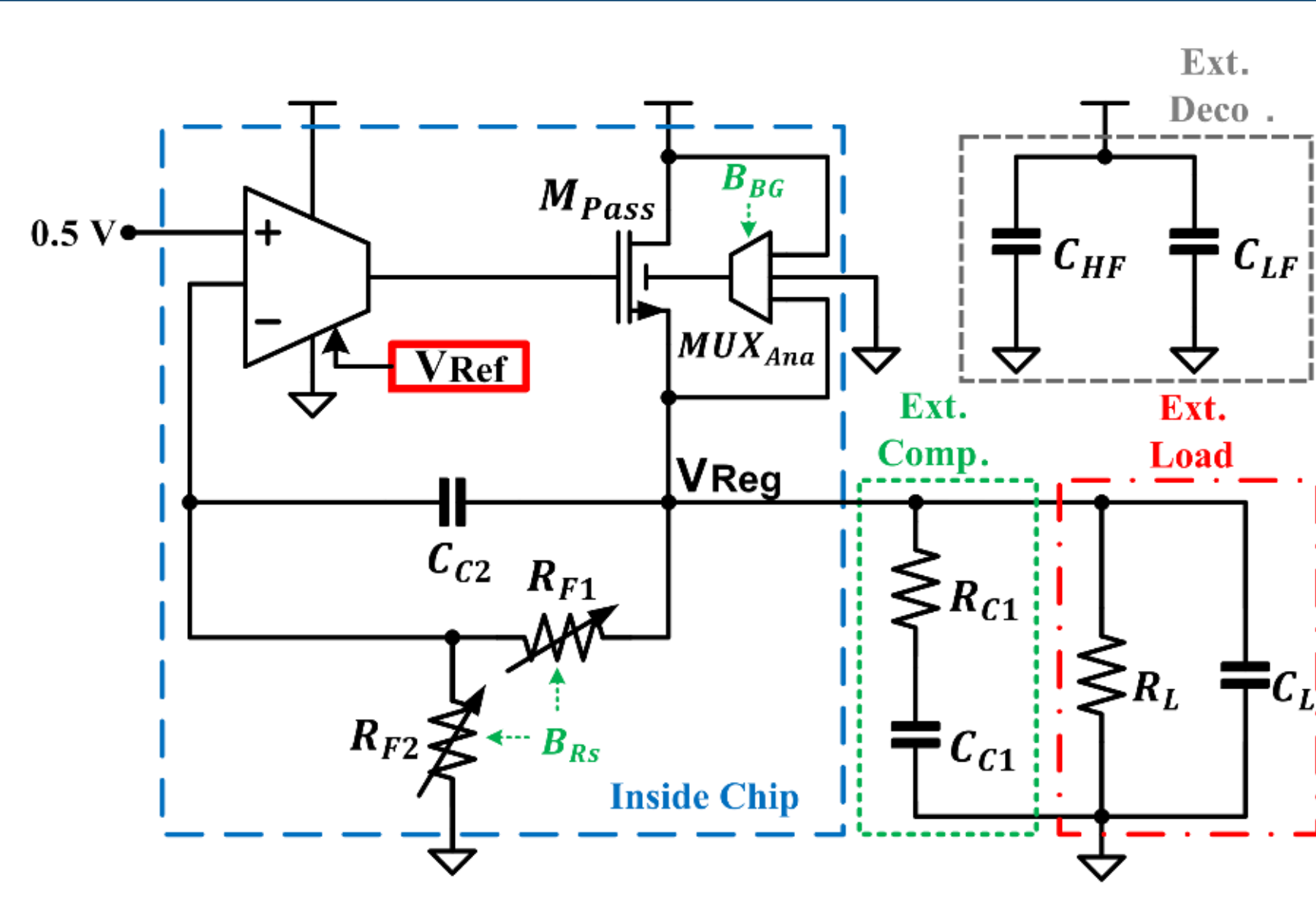


Fig. 2: Cryogenic voltage regulator, with its components integrated on chip and external elements.

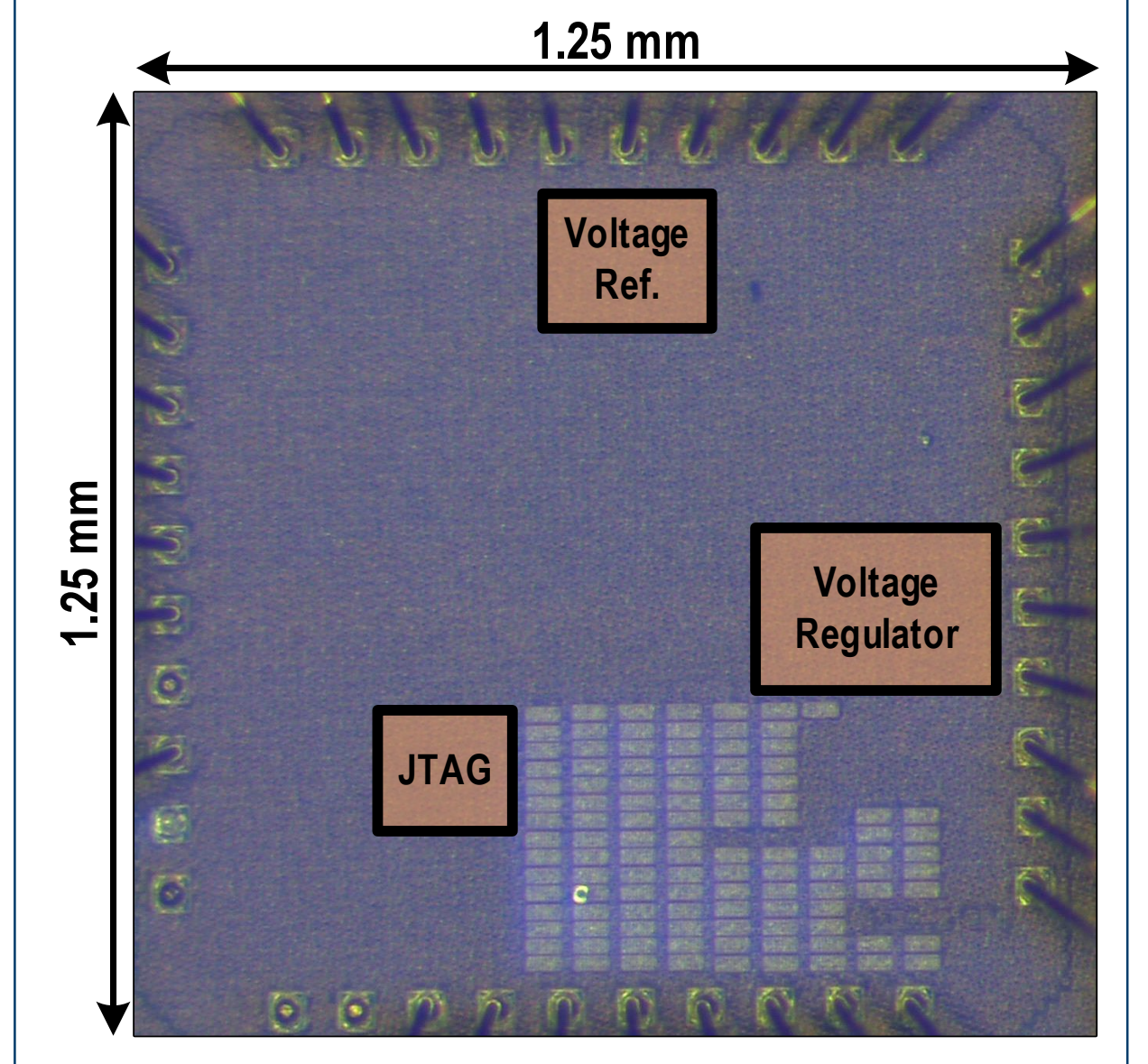


Fig. 3: Micrograph of a prototype IC manufactured in a commercial 22 nm FDSOI Technology.

## 1. MOTIVATION

- High performance Integrated Circuits (ICs) are a fundamental part of future Quantum Computers (QCs) [1].
- The ICs of QCs need regulated, stable and noise free supply voltages [2].
- Supply voltage lines in dilution fridges are prone to voltage ripple noise due to pulse tube vibrations, ground loops induce noise and dynamic load currents [3], [4].
- Cryogenic ICs for in situ voltage regulation can provide a clean voltage supply for the ICs of QCs.
- A voltage reference and a voltage regulator are presented as building blocks for cryogenic voltage regulation.
- The investigated circuits were developed in 22 nm FDSOI technology and tested from 6 K to 300 K.

## 2. INTEGRATED CIRCUITS DESCRIPTION

- The voltage reference circuit (Fig. 1) uses the cryogenic  $V_{th}$  saturation phenomenon as working principle.
- The circuit is composed of current sources that bias a diode connected NMOS device to yield the output reference voltage ( $V_{Ref}$ ).
- $V_{Ref}$  is a temperature stable quantity used in analog signal processing.
- The voltage regulator (Fig. 2) employs an NMOS pass element whose back-gate terminal connection can be shifted by an analog multiplexer via a JTAG interface.
- Back-gate shifting allows the NMOS pass element  $V_{th}$  reduction for power optimization at cryogenic temperatures.
- The output regulated voltage ( $V_{Reg}$ ) can energize other cryogenic circuits with a stable power signal.
- The voltage reference, the voltage regulator and the JTAG interface are included in a prototype IC (Fig. 3) manufactured in a commercial 22 nm FDSOI technology.

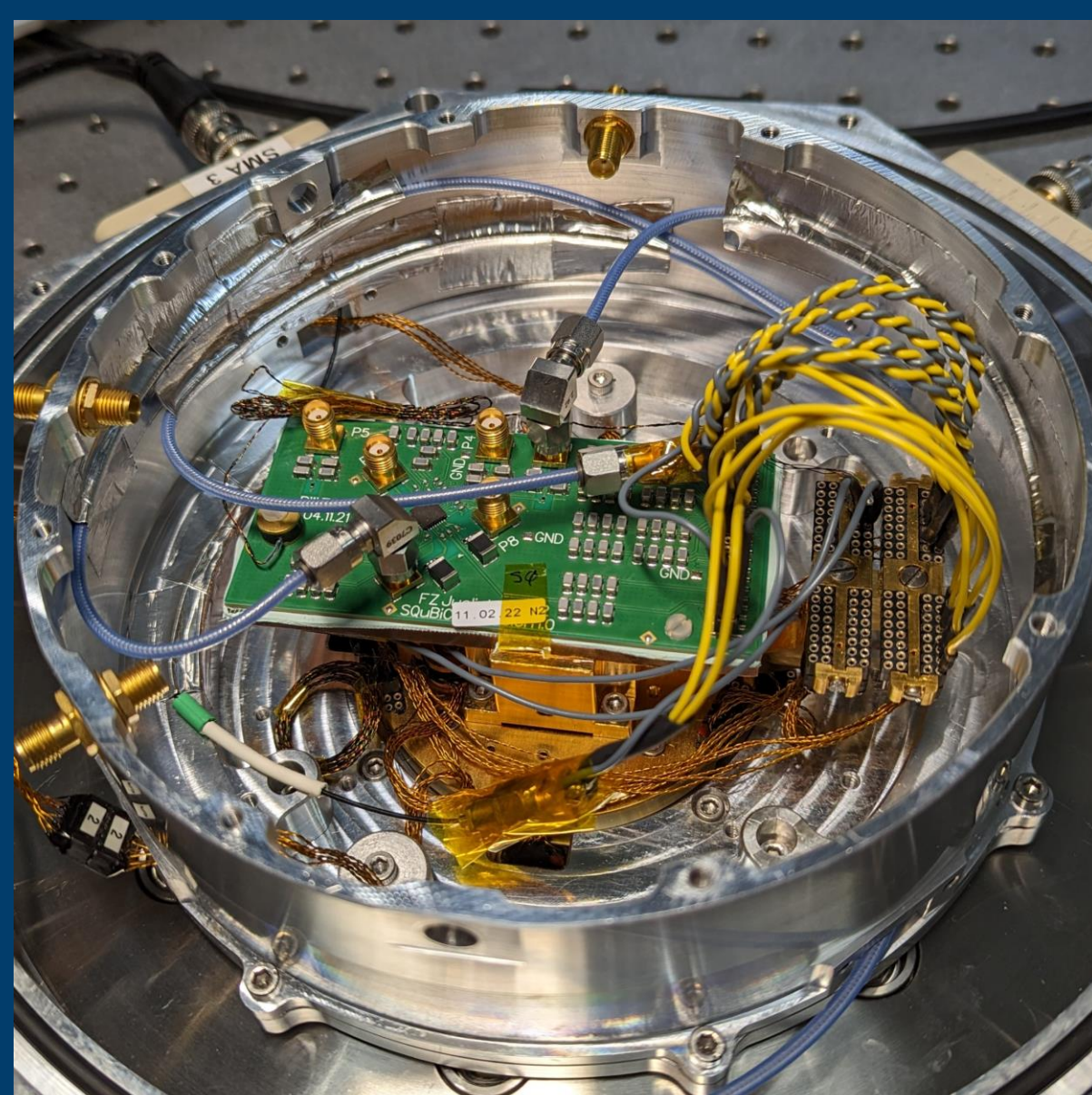


Fig. 4: Experimental setup: PCB with prototype IC, mounted onto the cryostat cold head (Gifford-McMahon cryocooler).

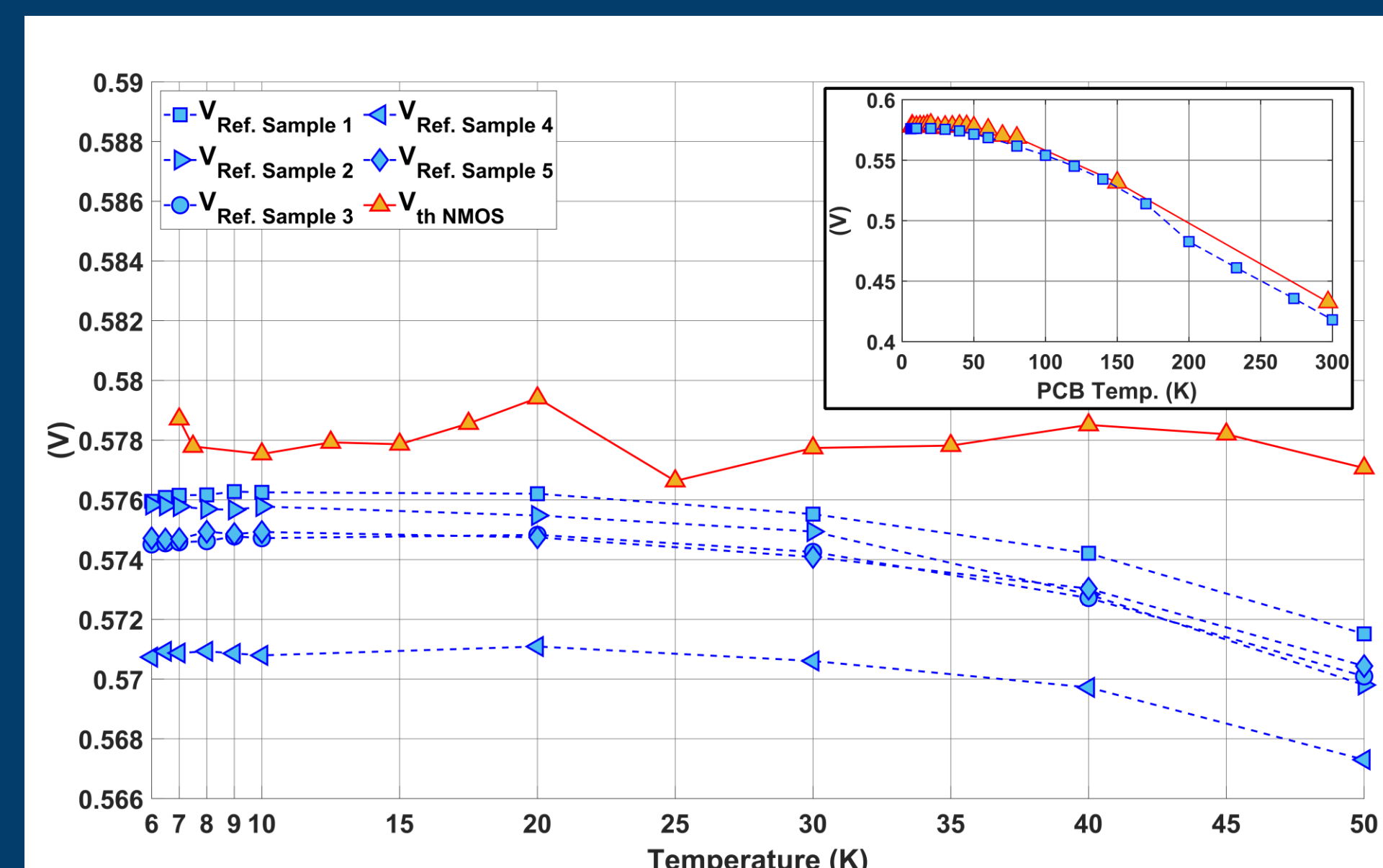


Fig. 5: Measured output from voltage reference over the temperature range of interest (6 K to 50 K), with  $V_{Sup} = 1.25$  V and  $V_{BG} = 0$  V; results correspond to 5 sample chips. Extracted  $V_{th}$  from I/O NMOS ( $W = 1$   $\mu$ m,  $L = 0.32$   $\mu$ m) is added for comparison. Inset displays sample 1 data over a wider temperature range (6 K to 300 K).

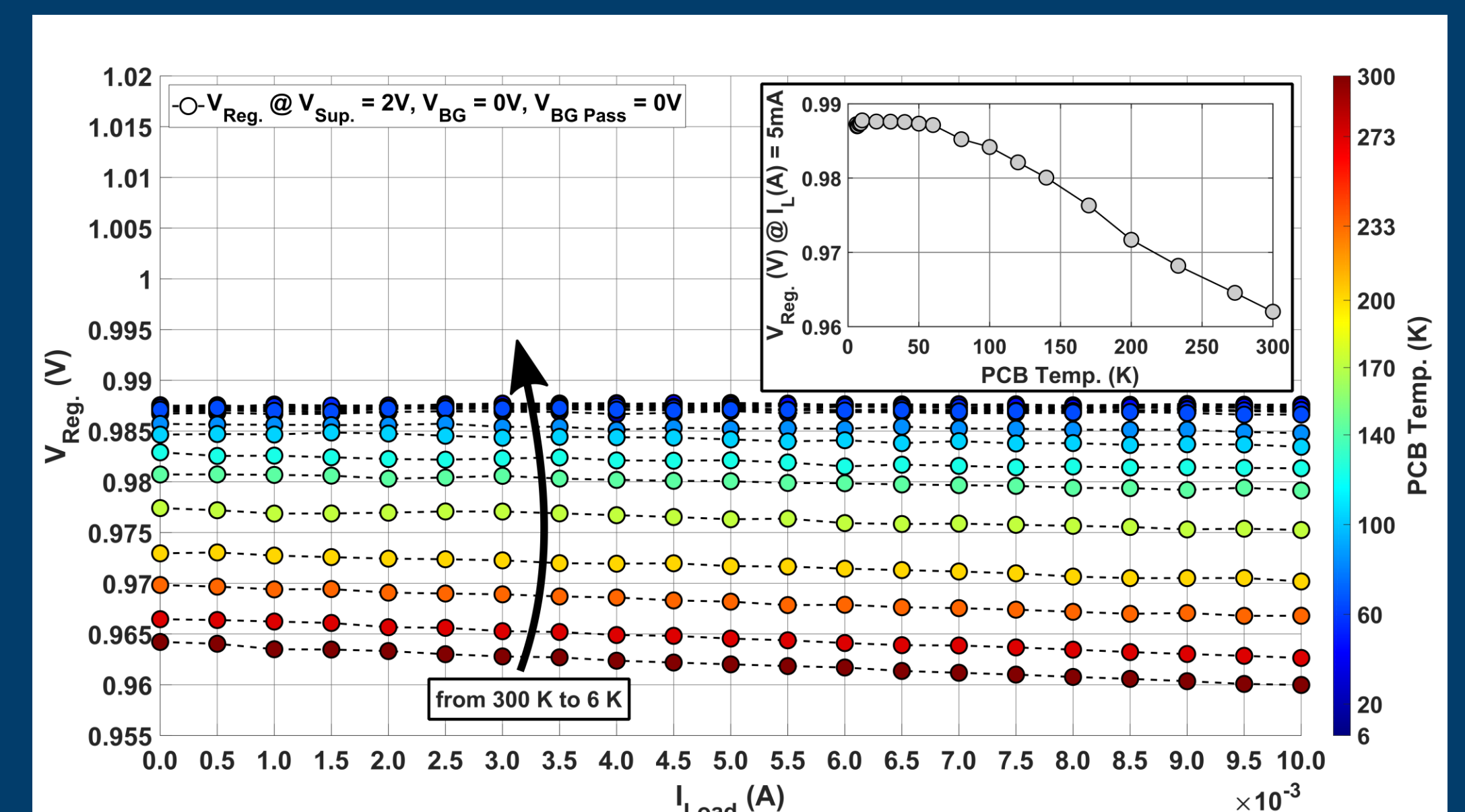


Fig. 6: Measured regulator output voltage ( $V_{Reg}$ ) in relation to  $I_{Load}$  and temperature, at  $V_{IN Ref} = 0.5$  V,  $R_{F1} = R_{F2}$ ,  $V_{BG} = 0$  V and  $V_{Sup} = 2$  V. Inset displays  $V_{Reg}$  for  $I_{Load} = 5$  mA over temperature (from 6 K to 300 K).

## 3. EXPERIMENTAL RESULTS

- A prototype IC is mounted over the cryostat cold head (Gifford-McMahon cryocooler) via a PCB specially designed for good thermal coupling (Fig. 4).
- Fig. 5 shows the response from the voltage reference circuit, with a temperature coefficient of 300 ppm/K, over the 6 K to 50 K range.
- Fig. 6 shows the voltage regulator response, with load regulation of 22 mV/A at 6 K.
- The studied circuits served as exploration vehicles to gain inside into the design and electrical characterization of cryogenic ICs [5], [6].



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<sup>1</sup> E. Charbon, F. Sebastiano, A. Vladimirescu, H. Homulle, S. Visser, L. Song, and R. M. Incandela, "Cryo-cmos for quantum computing," in 2016 IEEE International Electron Devices Meeting (IEDM), 2016, pp. 13.5.1–13.5.4.

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<sup>3</sup> K. Rachpon et al., "Vibration-induced electrical noise in a cryogen-free dilution refrigerator: Characterization, mitigation, and impact on qubit coherence," Review of Scientific Instruments, 2016, vol. 87, no 7.

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